

# High Temperature Experiments for Circuit Self-Recovery

Didier Keymeulen, Ricardo Zebulum, Vu Duong, Xin Guo<sup>\*</sup>, Ian Ferguson, and Adrian Stoica

Jet Propulsion Laboratory 4800 Oak Grove Drive,  
Pasadena, CA 91109, USA

[didier.keymeulen@jpl.nasa.gov](mailto:didier.keymeulen@jpl.nasa.gov)

**Abstract.** Temperature and radiation tolerant electronics, as well as long life survivability are key capabilities required for future NASA missions. Current approaches to electronics for extreme environments focus on component level robustness and hardening. Compensation techniques such as bias cancellation circuitry have also been employed. However, current technology can only ensure very limited lifetime in extreme environments. This paper presents a novel approach, based on evolvable hardware technology, which allows adaptive in-situ circuit redesign/reconfiguration during operation in extreme environments. This technology would complement material/device advancements and increase the mission capability to survive harsh environments. The approach is demonstrated on a mixed-signal programmable chip, which recovers functionality until 280°C. We show in this paper the functionality recovery at high temperatures for a variety of circuits, including rectifiers, amplifiers and filters.

## 1 Introduction

In-situ planetary exploration requires extreme-temperature electronics able to operate in low temperatures, such as below  $-220^{\circ}\text{C}$  on Neptune ( $-235^{\circ}\text{C}$  for Triton and Pluto) or high temperatures, such as above  $470^{\circ}\text{C}$  as needed for operation on the surface of Venus. Extrapolations of current developments indicate that hot electronics technology for  $>400^{\circ}\text{C}$  environments may not be ready in time for the 2006-2007 missions, except possibly for “grab-and-go” or “limited life” operations [1]. For extended missions, innovative approaches are needed. Terrestrial applications include combustion systems, well logging, nuclear reactors and dense electronic packages.

The maximum working temperature for semiconductors can be estimated from their intrinsic carrier density, which depends on the band-gap of the material. When the intrinsic density reaches the doping level of the devices, electrical parameters are expected to change drastically [2]. For the high-voltage regime (1000V), the theoretical limit for silicon is  $150^{\circ}\text{C}$ ; for discrete devices below 100V, it is expected about  $250^{\circ}\text{C}$  [2]. Materials used up to  $300^{\circ}\text{C}$  include bulk silicon and silicon-on-insulator (SOI) technologies; for higher temperatures, gallium arsenide (GaAs), silicon carbide (SiC), and diamond show promise, and devices have been

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<sup>\*</sup> Chromatech Alameda CA 94501

demonstrated at 500°C [3]. A survey of high-temperature effects and design considerations is found in [4]. A review of the physical limits and lifetime limitations of semiconductor devices at high-temperatures is found in [2].

In addition to material/device solutions, circuit solutions for the compensation of the effects of temperature have also been employed. Circuit solutions that compensate offset voltage and current leakage problems are described for example in [3], where several circuit topologies for high-temperature design, including a continuous-time auto-zeroed OpAmp and an A/D circuit that uses error suppression to overcome high-temperature leakages, are given. Another circuit for high-temperature operation with current leakage compensation is presented in [5]. Bias cancellation techniques for high-temperature analog application are presented in [6].

All the above solutions are fixed circuit design solutions, and satisfy the operational requirements only over a given temperature range. Once the limits of the range are exceeded, the performance deteriorates and cannot be recovered. In this paper, we propose the use of reconfigurable chips, which allow for a large number of topologies to be programmed, some more suitable for high-temperature. The interconnections between components can be changed, and new circuits can be configured, in an arrangement that uses the on-chip components/devices *at the new operational point on their characteristics*. In essence, a new design process takes place automatically, in-situ, under the control of a search algorithm. The configurations could be determined either before launch - part of the original design (which would identify good configurations and store them in a memory) - or in-situ. At the higher temperatures, once the performance of the current topology starts to deteriorate, the system would switch to a more suitable topology.

Reconfiguration can be controlled by evolutionary algorithms, a research area called Evolvable Hardware (EHW). Evolvable hardware technology is particularly significant to future NASA autonomous systems, providing on-board resources for reconfiguration to self-adapt to situations, environments and mission changes. It would enable future space missions using concepts of spacecraft surviving in excess of 100 years as well as electronics for temperatures over 460°C as encountered on the surface of Venus which pose challenges to current electronics. In addition, this technology can be used to reduce massive amounts of sensor data to lean data sent to centralized digital systems.

As part of an effort to develop evolution-oriented devices for Evolvable Hardware experiments, we designed and fabricated a series of Field Programmable Transistor Array (FPTA) chips in 0.5 micron and 0.18 micron bulk CMOS. These chips are reconfigurable at transistor level and were used to demonstrate on-chip evolution/synthesis of a variety of conventional building blocks for electronic circuits such as logical gates, transconductance amplifiers, filters, Gaussian neurons, data converters, etc [7], [8].

We present results on using evolution to recover the functionality of FPTA-mapped circuits affected by changes in temperature. In this paper we present a more detailed account of the evolutionary recovery, and explain how temperature degradation can fundamentally impact the intended function of the IC. The examples chosen include analog circuits whose behavior deteriorates as the temperature increase, thus totally altering the intended analog function. Evolution is able to find alternate circuits that perform correctly at the higher temperature.

The paper is organized as follows: Section 2 presents the details on a FPTA-2 chip developed as an evolution-oriented architecture for reconfigurable hardware, and introduces the experimental high temperature testbed. Section 3 presents experiments that illustrate that evolution-guided reconfiguration can recover functionality deteriorated/alterd by increased temperature. Section 4 concludes the work.

## 2 Structure of Evolvable Systems

An evolvable hardware system is constituted of two main components: reconfigurable hardware (RH) and an evolutionary processor (EP) that acts as a reconfiguration mechanism. In the evolvable systems we built for this effort, the EP was implemented and ran on a stand-alone DSP board. The RH was embodied in the form of a Field Programmable Transistor Array (FPTA-2) architecture, a custom made chip fabricated in silicon. This section will refer to the general characteristics of the two components and will also describe the Evolvable System testbed for high temperature experiments.

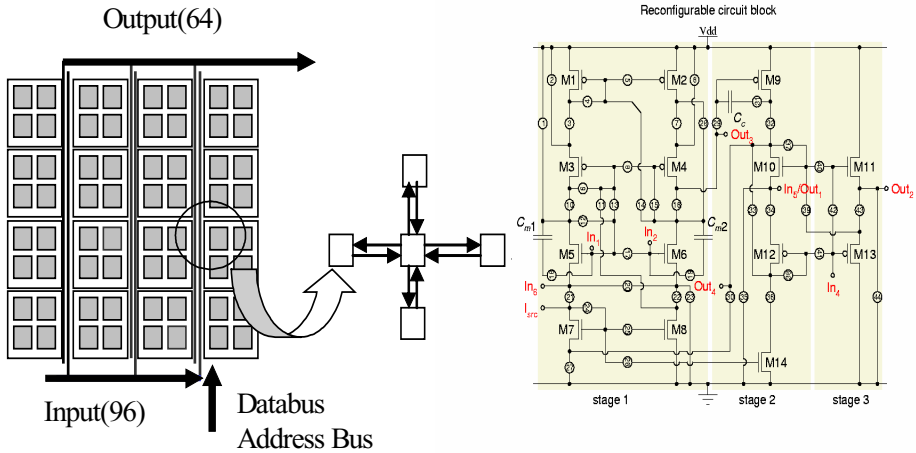
### 2.1 The FPTA

The FPTA is an evolution-oriented reconfigurable architecture (EORA) [8] with configurable granularity at the transistor level. It can map analog, digital and mixed signal circuits. The architecture is cellular, with each cell having a set of transistors, which can be interconnected by other “configuration transistors”. For brevity, the “configuration transistors” are called switches. However, unlike conventional switches, these can be controlled for partial opening, with appropriate voltage control on the gates, thus allowing for transistor-resistor type topologies.

Cells are interconnected to local neighbors with switches. A variety of simple circuits can be mapped onto this device or on multiple devices by cascading them. Its design was inspired by observing a variety of analog designs in which transistors often come in rows of pairs of transistors (for various current mirrors, differential pairs etc.), and have an average of four rows between VDD and ground. More rows can be ensured cascading cells, while fewer rows can be mapped by closing some switches to bypass rows.

The FPTA-2 is a third generation of reconfigurable chips designed at JPL, consisting of an 8x8 array of re-configurable cells. It was fabricated using TSMC 0.18u/1.8V technology. Each cell has a transistor array as well as a set of programmable resources, including programmable resistors and static capacitors. Figure 1 provides a broad view of the chip architecture together with a detailed view of the reconfigurable transistor array cell. The re-configurable circuitry consists of 14 transistors connected through 44 switches. The re-configurable circuitry is able to implement different building blocks for analog processing, such as two and three stages OpAmps, logarithmic photo detectors, or Gaussian computational circuits. It includes three capacitors, Cm1, Cm2 and Cc, of 100fF, 100fF and 5pF respectively. Control signals

come on the 9-bit address bus and 16-bit data bus, and access each individual cell providing the addressing mechanism for downloading the bit-string configuration of each cell. A total of ~5000 bits is used to program the whole chip. The pattern of interconnection between cells is similar to the one used in commercial FPGAs: each cell interconnects with its north, south, east and west neighbors.



**Fig. 1.** FPTA 2 architecture (left) and schematic of cell transistor array (right). The cell contains additional capacitors and programmable resistors (not shown).

## 2.2 A Stand-Alone Board-Level Evolvable System

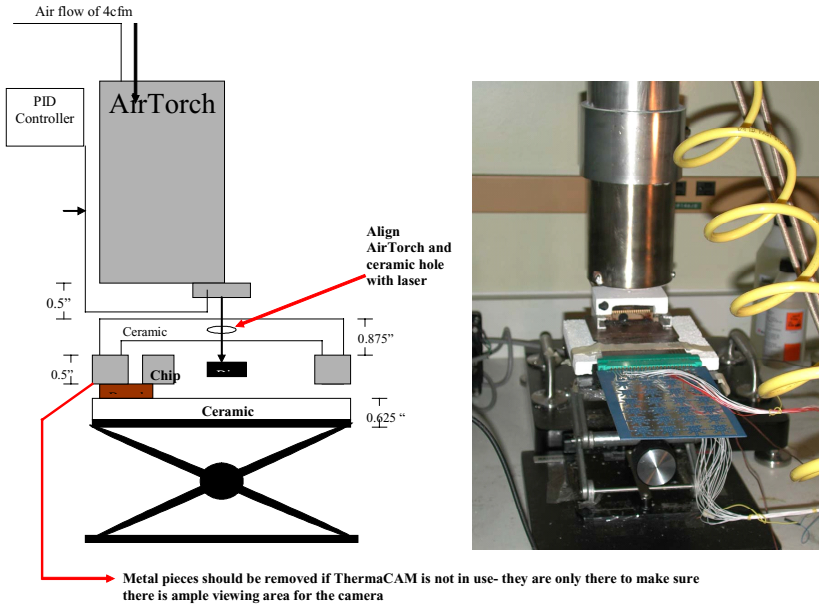
A complete stand-alone board-level evolvable system (SABLES) was built by integrating the FPTA-2 and a DSP implementing the EP. The system is connected to the PC only for the purpose of receiving specifications and communicating back the result of evolution for analysis. The system fits in a box 8" x 8" x 3". Communication between DSP and FPTA is very fast with a 32-bit bus operating at 7.5MHz. The FPTA can be attached to a Zif socket attached to a metal electronics board to perform extreme temperature experiments. The evaluation time depends on the tests performed on the circuit. Many of the tests attempted here require less than two milliseconds per individual, and runs of populations of 100 to 200 generations require only 20 seconds.

## 2.3 Extreme Temperature Testbed

The purpose of this testbed is to achieve temperatures exceeding 350°C on the die of the FPTA-2 while staying below 280°C on the package. It is necessary to stay below 280°C on the package in order not to destroy the interconnects and package integrity. Die temperatures should stay below 400°C to make sure die attach epoxy does not soften and that the crystal structure of the aluminum core does not soften. To achieve

these high temperatures the testbed includes an Air Torch system. The Air Torch is firing hot compressed air through a small hole of a high temperature resistance ceramic protecting the chip. To measure temperature Thermocouples were used.

Figure 2 shows the Air Torch apparatus electronically controlled by PID controller, which maintains a precision of  $\pm 10^\circ\text{C}$  up to  $1000^\circ\text{C}$ . Figure 2 shows also the ceramic protecting the die connections and the package. The Temperature was measured above the die and under the die using thermocouples.



**Fig. 2.** Experimental Setup for Extreme Temperature Experiments for the FPTA.

### 3 Extreme Temperature Experiments

We describe here experiments for evolutionary recovery of the functionality of the following circuits:

- Halfwave Rectifier at  $280^\circ\text{C}$
- Closed Loop OpAmp at  $245^\circ\text{C}$
- Low Pass Filters at  $230^\circ\text{C}$

The rationale of these experiments was of first evolving the proposed circuits at room temperature. After the functionality is achieved the temperature is increased using the apparatus shown in Figure 2, until the functionality is degraded. When the device characteristics change with temperature, one can preserve the function by finding a different circuit (topology) solution, which exploits the altered/modified characteristics. Therefore, in order to recover the functionality, the evolutionary process is started again at high temperature. Evolution can obtain a circuit that works

at high temperature if the search process is carried on at the temperature in which the circuit is supposed to work.

One limitation of these experiments is the fact that we assume the Evolutionary Processor as fault-free, i.e. the DSP implementing the Evolutionary Algorithm is always at room temperature. Further studies should be performed to investigate the effect of high temperature in the device implementing the Evolutionary Algorithm.

### 3.1 Half Wave Rectifier on FPTA-2 at 280°C

The objective of this experiment is to recover functionality of a half wave rectifier for a 2kHz sine wave of amplitude 2V using only two cells of the FPTA-2 at 280°C. The fitness function given below does a simple sum of error between the target function and the output from the FPTA.

The input was a 2kHz excitation sine wave of 2V amplitude, while the target waveform was the rectified sine wave. The fitness function rewarded those individuals exhibiting behavior closer to target (by using a sum of differences between the response of a circuit and the target) and penalized those farther from it. The fitness function was:

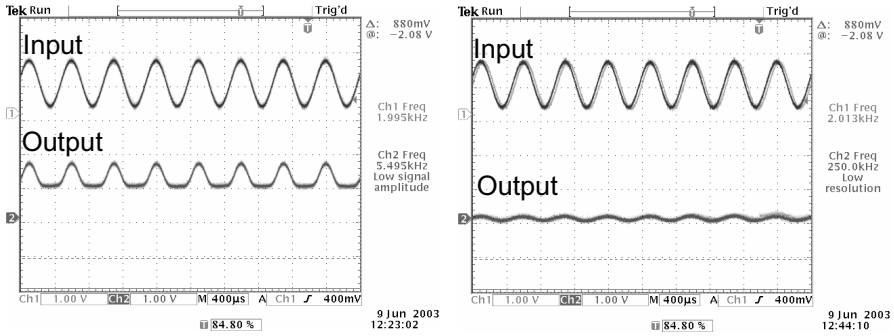
$$F = \sum_{t_s=0}^{n-1} \begin{cases} R(t_s) - S(t_s) & \text{for } (t_s < n/2) \\ R(t_s) - V_{\max} / 2 & \text{otherwise} \end{cases} \quad (1)$$

where  $R(t_s)$  is the circuit output,  $S(t_s)$  is the circuit stimulus,  $n$  is the number of sampled outputs, and  $V_{\max}$  is 2V (the supply voltage). The output must follow the input during half-cycle, staying constant at a level of half way between the rails (1V) in the other half.

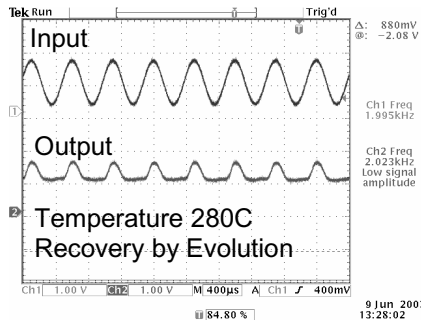
After the evaluation of 100 individuals, they were sorted according to fitness and a 9% (elite percentage) portion was set aside, while the remaining individuals underwent crossover (70% rate), either among themselves or with an individual from the elite, and then mutation (4% rate). The entire population was then reevaluated. Only two cells of the FPTA were allocated and used in this experiment.

The fitness function in equation (1) should be minimized. At room temperature the initial population has an average fitness of 100,000 and the final solution achieves a fitness around 4,500 [10]. At increased temperatures the fitness of the circuit solution is slightly worse, being around 6,000.

Figure 3 depicts the response of the evolved circuit at room temperature and the degraded response at high temperature. Figure 4 shows the response of circuit obtained by running evolution at 280°C, where we can see that the functionality is recovered.



**Fig. 3.** Input and output waves of the half-wave rectifier. At the left we show the response of the circuit evolved at 27°C. At the right we show the degraded response of the same circuit when the temperature is increased to 280°C.



**Fig. 4.** The solution for the Half wave rectifier at 280°C.

### 3.2 Amplifier Circuit Using Closed Loop OpAmp at 245°C

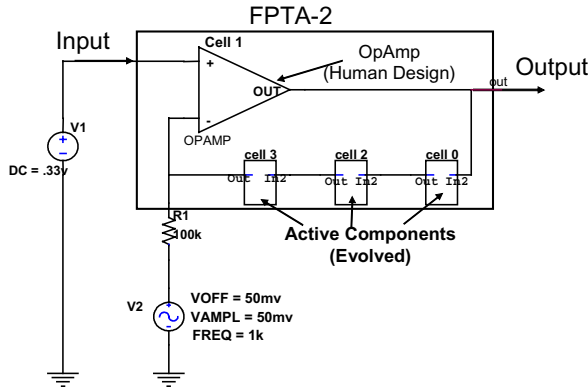
The objective of this experiment is to recover by evolution the functionality of a circuit that can provide a gain using compensation circuit introduced in the feedback loop of a conventional OpAmp implemented on the FPTA-2. Amplifiers are a very important building block in sensor circuits and it has been verified in this experiment that three FPTA cells can accomplish this task. One sine wave of 50mV amplitude and 1kHz frequency was applied as stimulus and the target output was a sine wave of twice the amplitude. The fitness encompassed the absolute sum of errors between the FPTA output,  $R(t)$ , and the target,  $T(t)$  as shown below.

$$F = \sum_{t=0}^{n-1} | (R(t) - T(t)) | \quad (2)$$

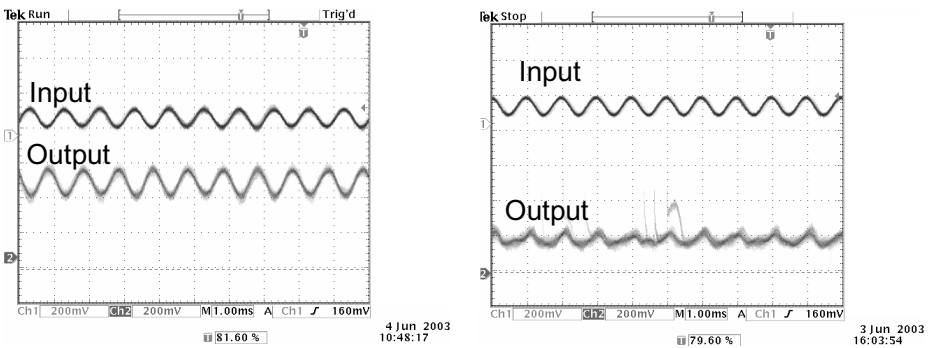
The other Evolutionary Algorithm parameters were similar to the ones described in the previous section.

Figure 5 illustrates the block diagram of the circuit in the FPTA-2. One cell of the chip implements a conventional OpAmp, while 3 re-configurable cells in a feedback loop have their configurations changed by evolution to achieve a compensating structure providing a voltage gain of 2.

Figure 6 shows the response of the circuit evolved at room temperature and the degraded functionality. Figure 7 depicts the recovered response of the circuit evolved at 245°C.



**Fig. 5.** Block diagram of the closed-loop amplifier implemented in the FPTA-2. Cell 1 realizes a conventional OpAmp; cells 0, 2 and 3 are evolved to provide an amplification gain of 2.



**Fig. 6.** Degradation of the amplifier circuit. At the left response at room temperature, at the right response at 245°C.

### 3.3 Low Pass Filter at 230°C

The objective of this experiment is to recover the functionality of a low-pass filter given ten cells of the FPTA-2. The fitness function given below performs a sum of error between the target function and the output from the FPTA in the frequency domain.



$$F = \sum_{f_s=0}^{n-1} (R(f) - T(f)) \quad (3)$$

Given two tones at 1kHz and 10kHz, the objective is to have at the output only the lowest frequency tone (1kHz). This hardware evolved circuit demonstrated that the FPTA-2 is able to recover active filters with some gain at 230°C. Ten FPTA cells were used in this experiment.

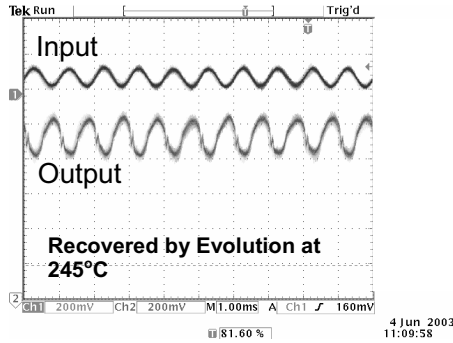


Fig. 7. The solution for the recovered amplifier circuit

Figure 8 shows the response of the evolved filter at room temperature and degradation at 230°C. Figure 9 displays the same information in the frequency domain. Figure 10 shows the time and frequency response of the recovered circuit evolved at 230°C.

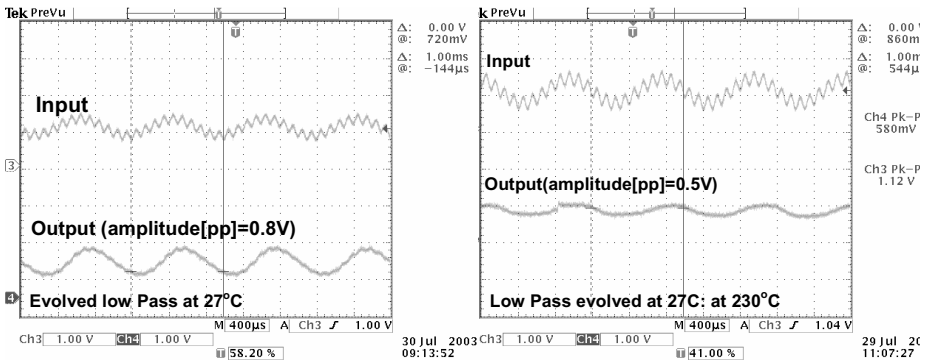
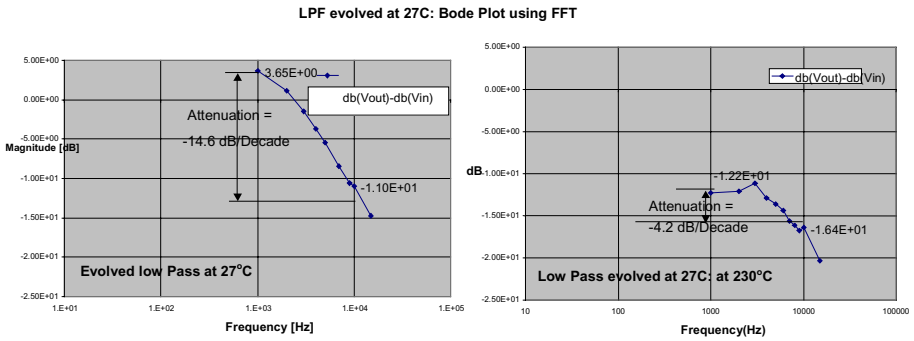
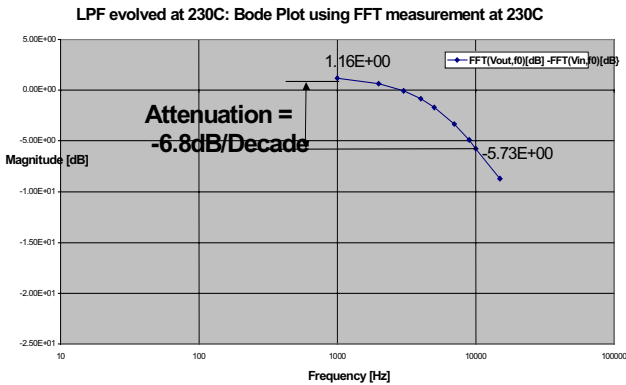
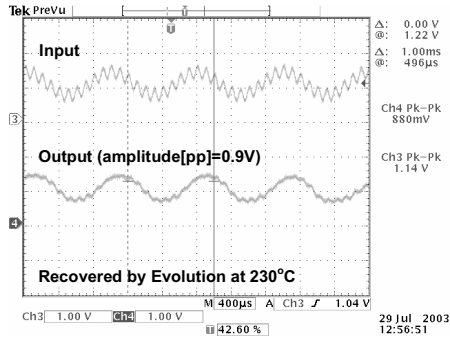


Fig. 8. Low-Pass Filter. The graph in the left displays the input and output signals in the time domain. The graph in the right shows the input and output in the time domain when the FPTA-2 was submitted to temperature of 230°C (Circuit stimulated by two sine waves: 1kHz and 10kHz).



**Fig. 9.** Low-Pass Filter. The graph in the left displays the frequency response of the output signal at room temperature. The graph in the right shows the frequency response of the output when the FPTA-2 was submitted to temperature of 230°C. (Circuit was stimulated by a sine wave with a frequency sweeping from 1kHz and 10kHz).



**Fig. 10.** Low-Pass Filter. The graph at the top shows the circuit input stimulus and response in the time domain (Time response was obtained using a stimulation signal made of two sine waves: 1kHz and 10kHz – Frequency response was obtained by sweeping a frequency from 1kHz to 10kHz). The graph at the bottom displays the Bode diagram of the output signals.

At room temperature, the originally evolved circuit presents a gain of 3dB at 1kHz and a roll-off of -14dB/dec. When the temperature is increased to 230°C, the roll-off

goes to -4dB/dec and the gain at 1kHz falls to -12dB. In the recovered circuit at high temperature the gain at 1kHz is increased back to 1dB and the roll-off goes to -7dB/dec. Therefore the evolved solution at high temperature is able to restore the gain and to partially restore the roll-off.

All the recovery experiments described above were performed for a maximum temperature of 280°C. For temperatures higher than 280°C, it was observed that the FPTA switch elements work as a fixed resistance (partly closed switch) regardless of the control voltage. This incorrect behavior, due to increase of parasitic currents at high temperature, turns unfeasible evolutionary recovery experiments for temperatures higher than 280°C for this particular type of technology.

## 4 Conclusions

The experiments demonstrate the possibility of using evolutionary self-configuration to recover functionality lost at extreme temperatures (up to 280°C). In addition, evolutionary design can be used to create designs targeted to the extreme temperatures. One should mention here that while a device may work at a certain temperature, the real limiting factors for applications will be failure rates and lifetimes. The experiments were performed on bulk CMOS because of the convenience and low cost of fabricating in this technology. For maximum performance, evolvable hardware should make use of an enhancing technique combined with materials/devices more appropriate for extreme temperatures, such as SiC, etc.

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